

**IN THE CLAIMS:**

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. When strikethrough cannot easily be perceived, or when five or fewer characters are deleted, [[double brackets]] are used to show the deletion. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered). Please AMEND claim 3, and ADD new claim 6 in accordance with the following:

1. (cancelled)

2. (cancelled)

3. (currently amended) A dynamic burn-in apparatus for a semiconductor device, wherein a signal output from a signal generator is provided to a semiconductor device to be tested in the burn-in tank, comprising:

a converter that is added at the output of the signal generator and located outside of a substrate supporting the semiconductor device, wherein the frequency of the signal output from the signal generator is increased by the converter and the signal output from the converter is provided to the semiconductor device.

4. (previously presented) A dynamic burn-in apparatus of claim 3, wherein the converter comprises a synchronous oscillator and a waveform shaping circuit,

wherein the synchronous oscillator is synchronized with a clock output from the signal generator and generates a clock having higher frequency than that of the clock output from the signal generator, and the waveform shaping circuit shapes a control signal, a data signal and an address signal output from the signal generator into the control signal, the data signal and the address signal that have the width corresponding to the clock output from the synchronous oscillator,

wherein the clock output from the synchronous oscillator and the control signal, the data signal and the address signal output from the waveform shaping circuit are provided to the semiconductor device.

5. (previously presented) A dynamic burn-in apparatus for a semiconductor device, wherein a signal output from a signal generator is provided to a semiconductor device to be tested in a burn-in tank, comprising:

a converter that is arranged at the output of the signal generator, wherein the frequency of the signal output from the signal generator is increased by the converter and the signal output from the converter is provided to the semiconductor device,

wherein the semiconductor device is a general-purpose memory device, the converter comprises a synchronous oscillator and a waveform shaping circuit,

wherein the synchronous oscillator is synchronized with a clock output from the signal generator and generates a clock having higher frequency than that of the clock output from the signal generator, and the waveform shaping circuit shapes a control signal, a data signal and an address signal output from the signal generator into the control signal, the data signal and the address signal that have a width corresponding to the clock output from the synchronous oscillator, and

wherein the clock output from the synchronous oscillator and the control signal, the data signal and the address signal output from the waveform shaping circuit are provided to the semiconductor device.

6. (new) A dynamic burn-in apparatus for a semiconductor device, wherein a signal output from a signal generator is provided to a semiconductor device to be tested in a burn-in tank, comprising:

a converter arranged at the output of the signal generator and outside of a substrate supporting the semiconductor device, wherein the converter increases, by N times, N a positive integer, a frequency of the signal output from the signal generator and outputs the signal having the increased frequency to the semiconductor device to be tested in the burn-in tank to implement expedited dynamic burn-in, increasing a rate of detection of defects due to initial deterioration.